

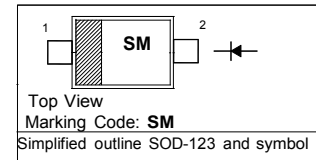
Surface Mount Schottky Barrier Diodes

Features

- Low forward voltage
- Low reverse capacitance

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	SD101AW	60
		SD101BW	50
		SD101CW	40
Reverse Voltage	V_R	SD101AW	60
		SD101BW	50
		SD101CW	40
Forward Continuous Current	I_{FM}	15	mA
Power Dissipation	P_d	400	mW
Non-Repetitive Peak Forward Surge Current	I_{FSM}	at $t = 1\text{ s}$	50
		at $t = 10\text{ }\mu\text{s}$	2
Operating and Storage Temperature Range	T_j, T_{stg}	- 65 to + 125	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Reverse Breakdown Voltage at $I_R = 10\text{ }\mu\text{A}$	$V_{(BR)R}$	SD101AW	60	-
		SD101BW	50	-
		SD101CW	40	-
Forward Voltage at $I_F = 1\text{ mA}$ at $I_F = 15\text{ mA}$	V_F	SD101AW	-	0.41
		SD101BW	-	0.4
		SD101CW	-	0.39
		SD101AW	-	1
		SD101BW	-	0.95
		SD101CW	-	0.9
Reverse Current at $V_R = 50\text{ V}$ at $V_R = 40\text{ V}$ at $V_R = 30\text{ V}$	I_R	SD101AW	-	200
		SD101BW	-	200
		SD101CW	-	200
Total Capacitance at $V_R = 0\text{ V}, f = 1\text{ MHz}$	C_T	SD101AW	-	2
		SD101BW	-	2.1
		SD101CW	-	2.2
Reverse Recovery Time at $I_F = I_R = 5\text{ mA}, I_{rr} = 0.1X I_R, R_L = 100\text{ }\Omega$	t_{rr}	-	1	ns

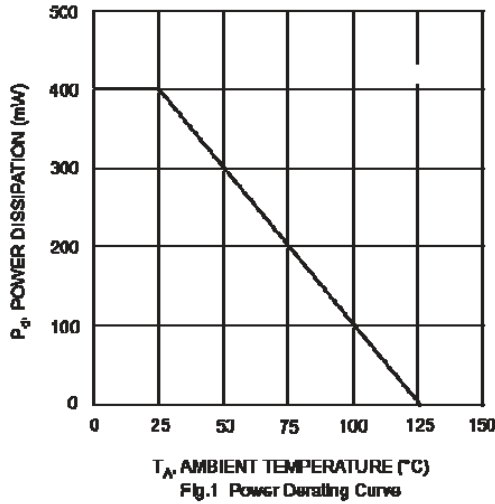


Fig. 1 Power Derating Curve

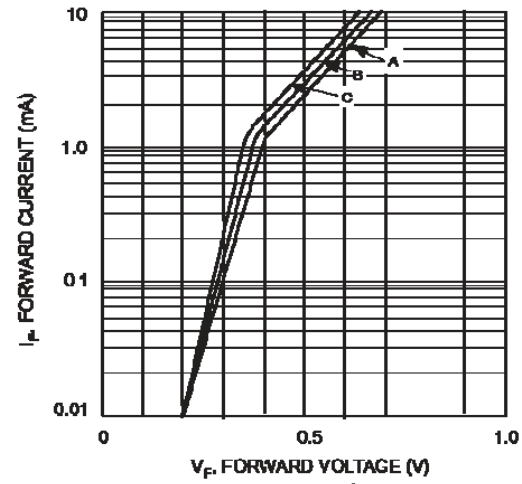


Fig. 2 Typical Forward Characteristic

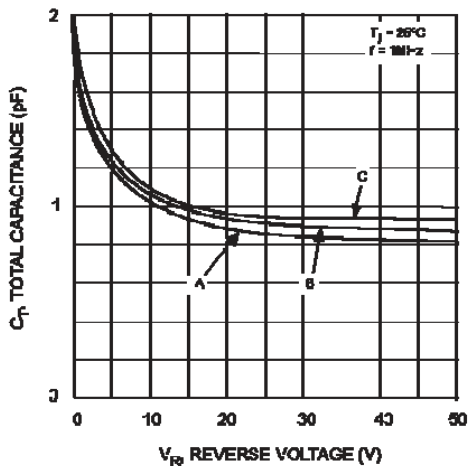


Fig. 3 Typical Total Capacitance vs Reverse Voltage

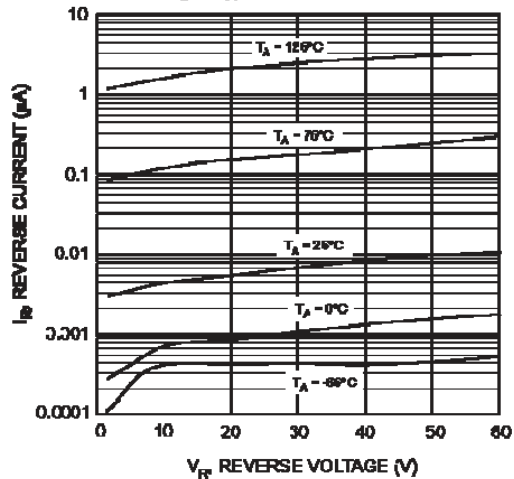


Fig. 4 Typical Reverse Characteristics



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SOD-123



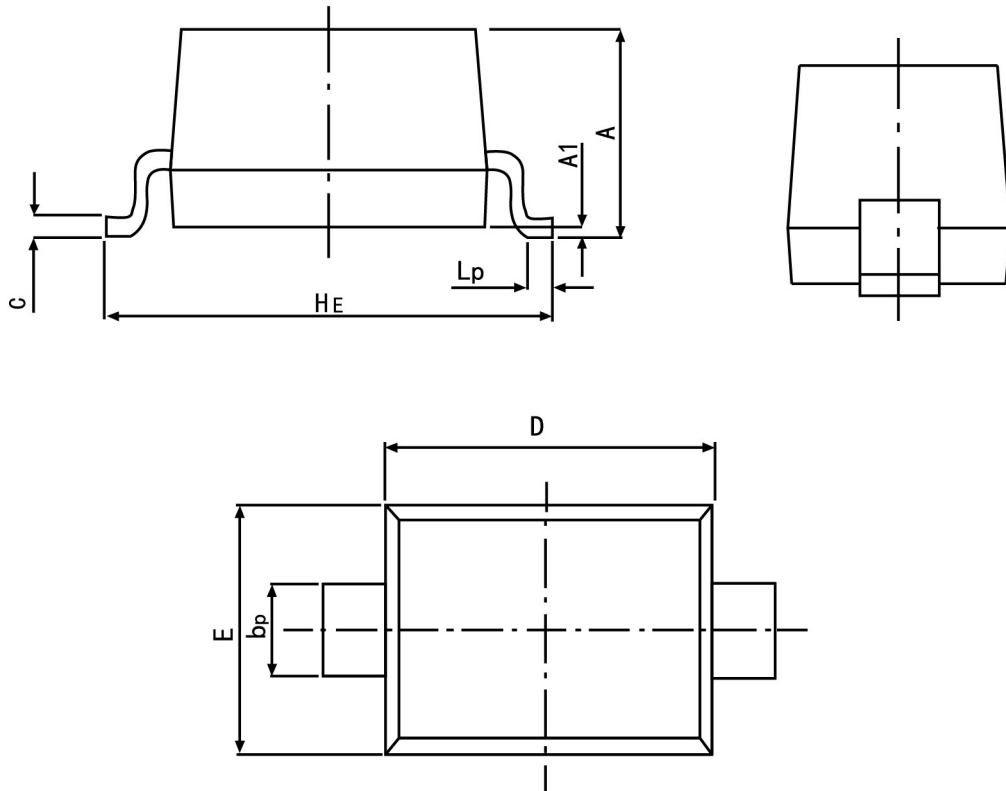
SD101AW-SD101CW

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PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-123



Symbol	Dimension in Millimeters	
	Min	Max
A	0.90	1.20
bp	0.50	0.60
C	0.100	0.135
D	2.55	2.75
E	1.55	1.65
HE	3.55	3.85
A1	0.01	0.10
Lp	0.20	0.50